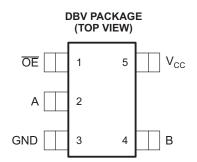
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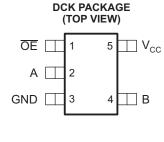
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#### **FEATURES**

- Output Voltage Translation Tracks V<sub>CC</sub>
- Supports Mixed-Mode Signal Operation on All Data I/O Ports
  - 5-V Input Down to 3.3-V Output Level Shift With 3.3-V V<sub>CC</sub>
  - 5-V/3.3-V Input Down to 2.5-V Output Level Shift With 2.5-V  $\rm V_{\rm CC}$
- 5-V-Tolerant I/Os, With Device Powered Up or Powered Down
- Bidirectional Data Flow With Near-Zero Propagation Delay
- Low ON-State Resistance  $(r_{on})$  Characteristics  $(r_{on} = 5 \Omega \text{ Typ})$
- Low Input/Output Capacitance Minimizes Loading (C<sub>io(OFF)</sub> = 5 pF Typ)
- Data and Control Inputs Provide Undershoot Clamp Diodes

- Low Power Consumption (I<sub>CC</sub> = 20 μA Max)
- V<sub>CC</sub> Operating Range From 2.3 V to 3.6 V
- Data I/Os Support 0- to 5-V Signaling Levels (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.3 V, 5 V)
- Control Inputs Can Be Driven by TTL or 5-V/3.3-V CMOS Outputs
- I<sub>off</sub> Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- ESD Performance Tested Per JESD 22
  - 2000-V Human-Body Model (A114-B, Class II)
  - 1000-V Charged-Device Model (C101)
- Supports Digital Applications: Level Translation, USB Interface, Bus Isolation
- Ideal for Low-Power Portable Equipment





See mechanical drawings for dimensions.

#### **DESCRIPTION/ORDERING INFORMATION**

The SN74CB3T1G125 is a high-speed TTL-compatible FET bus switch with low ON-state resistance ( $r_{on}$ ), allowing for minimal propagation delay. The device fully supports mixed-mode signal operation on all data I/O ports by providing voltage translation that tracks  $V_{CC}$ . The SN74CB3T1G125 supports systems using 5-V TTL, 3.3-V LVTTL, and 2.5-V CMOS switching standards, as well as user-defined switching levels (see Figure 1).

The SN74CB3T1G125 is a 1-bit bus switch with a single ouput-enable ( $\overline{OE}$ ) input. When  $\overline{OE}$  is low, the bus switch is ON, and the A port is connected to the B port, allowing bidirectional data flow between ports. When  $\overline{OE}$  is high, the bus switch is OFF, and a high-impedance state exists between the A and B ports.

#### **ORDERING INFORMATION**

T <sub>A</sub>	PACKA	GE <sup>(1)</sup>	ORDERABLE PART NUMBER	TOP-SIDE MARKING(2)
-40°C to 85°C	SOT (SOT-23) - DBV	Reel of 3000	SN74CB3T1G125DBVR	W25_
	SOT (SC-70) - DCK	Reel of 3000	SN74CB3T1G125DCKR	WM_

<sup>(1)</sup> Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

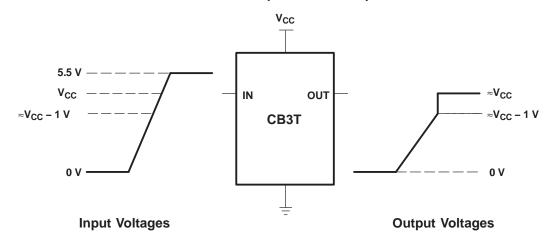
<sup>(2)</sup> The actual top-side marking has one additional character that designates the assembly/test site.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



## **DESCRIPTION/ORDERING INFORMATION (CONTINUED)**



NOTE A: If the input high voltage ( $V_{IH}$ ) level is greater than or equal to  $V_{CC} - 1$  V, and less than or equal to 5.5 V, then the output high voltage ( $V_{OH}$ ) level will be equal to approximately the  $V_{CC}$  voltage level.

Figure 1. Typical DC Voltage Translation Characteristics

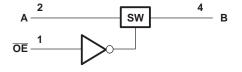
This device is fully specified for partial-power-down applications using  $I_{\text{off}}$ . The  $I_{\text{off}}$  feature ensures that damaging current will not backflow through the device when it is powered down. The device has isolation during power off.

To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

#### **FUNCTION TABLE**

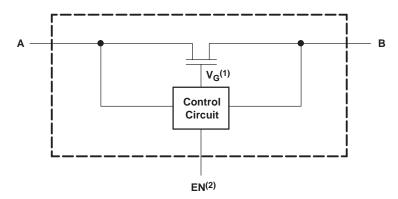
INPUT OE	INPUT/OUTPUT A	FUNCTION
L	В	A port = B port
Н	Z	Disconnect

## **LOGIC DIAGRAM (POSITIVE LOGIC)**



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## SIMPLIFIED SCHEMATIC, EACH FET SWITCH (SW)



- (1) Gate voltage (V<sub>G</sub>) is equal to approximately V<sub>CC</sub> + V<sub>T</sub> when the switch is ON and V<sub>I</sub> > V<sub>CC</sub> + V<sub>T</sub>.
- (2) EN is the internal enable signal applied to the switch.

## Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

				MIN	MAX	UNIT	
$V_{CC}$	Supply voltage range			-0.5	7	V	
V <sub>IN</sub>	Control input voltage range <sup>(2)(3)</sup>			-0.5	7	V	
V <sub>I/O</sub>	Switch I/O voltage range <sup>(2)(3)(4)</sup>				7	V	
I <sub>IK</sub>	Control input clamp current	V <sub>IN</sub> < 0			-50	mA	
I <sub>I/OK</sub>	I/O port clamp current	I/O port clamp current $V_{I/O} < 0$			-50	mA	
I <sub>IO</sub>	ON-state switch current <sup>(5)</sup>				±128	mA	
	Continuous current through V <sub>CC</sub> or GND				±100	mA	
0	Deal (6)	DBV package			206	2011	
$\theta_{JA}$	Package thermal impedance (6)	DCK package			252	°C/W	
T <sub>stg</sub>	Storage temperature range			-65	150	°C	

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to ground, unless otherwise specified.
- (3) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (4)  $V_I$  and  $V_O$  are used to denote specific conditions for  $V_{I/O}$ .
- (5)  $I_{l}$  and  $I_{O}$  are used to denote specific conditions for  $I_{l/O}$ .
- (6) The package thermal impedance is calculated in accordance with JESD 51-7.

## Recommended Operating Conditions<sup>(1)</sup>

			MIN	MAX	UNIT
$V_{CC}$	Supply voltage		2.3	3.6	V
V	V <sub>CC</sub> = 2.3 V to		1.7	5.5	V
V <sub>IH</sub>	High-level control input voltage	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2	5.5	V
\/	Low-level control input voltage $ \frac{V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}}{V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}} $		0	0.7	V
$V_{IL}$			0	8.0	V
V <sub>I/O</sub>	Data input/output voltage		0	5.5	V
$T_A$	Operating free-air temperature		-40	85	°C

<sup>(1)</sup> All unused control inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

## SN74CB3T1G125 SINGLE FET BUS SWITCH 2.5-V/3.3-V LOW-VOLTAGE SWITCH WITH 5-V-TOLERANT LEVEL SHIFTER

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## Electrical Characteristics(1)

over recommended operating free-air temperature range (unless otherwise noted)

PAR	RAMETER	TEST CONDITIONS		MIN	TYP <sup>(2)</sup>	MAX	UNIT	
V <sub>IK</sub>		$V_{CC} = 3 \text{ V}, I_{I} = -18 \text{ mA}$			-1.2	V		
V <sub>OH</sub>		See Figure 3 and Figure 4						
I <sub>IN</sub>	Control inputs	V <sub>CC</sub> = 3.6 V, V <sub>IN</sub> = 3.6 V to 5.5 V or GND				±10	μΑ	
		V <sub>CC</sub> = 3.6 V,	$V_I = V_{CC} - 0.7 \text{ V to } 5.5 \text{ V}$			±20		
I <sub>I</sub>		Switch ON,	$V_{I} = 0.7 \text{ V to } V_{CC} - 0.7 \text{ V}$			-40	μΑ	
		$V_{IN} = V_{CC}$ or GND	$V_1 = 0 \text{ to } 0.7 \text{ V}$			±5		
I <sub>OZ</sub> (3)		$V_{CC} = 3.6 \text{ V}, V_O = 0 \text{ to } 5.5 \text{ V}, V_I = 0, \text{ Switch OFF}$	, V <sub>IN</sub> = V <sub>CC</sub> or GND			±10	μΑ	
I <sub>off</sub>		$V_{CC} = 0$ , $V_{O} = 0$ to 5.5 V, $V_{I} = 0$				10	μΑ	
1		$V_{CC} = 3.6 \text{ V}, I_{I/O} = 0,$	$V_I = V_{CC}$ or GND			20 μA		
Icc		Switch ON or OFF, $V_{IN} = V_{CC}$ or GND	V <sub>I</sub> = 5.5 V			20	20 μΑ	
$\Delta I_{CC}^{(4)}$	Control inputs	$V_{CC}$ = 3 V to 3.6 V, One input at $V_{CC}$ – 0.6 V, Ot	her inputs at V <sub>CC</sub> or GND			300	μΑ	
C <sub>in</sub>	Control inputs	$V_{CC} = 3.3 \text{ V}, V_{IN} = V_{CC} \text{ or GND}$			3		рF	
C <sub>io(OFF)</sub>		$V_{CC}$ = 3.3 V, $V_{I/O}$ = 5.5 V, 3.3 V, or GND, Switch	OFF, $V_{IN} = V_{CC}$ or GND		5		pF	
C		V <sub>CC</sub> = 3.3 V, Switch ON,	$V_{I/O} = 5.5 \text{ V or } 3.3 \text{ V}$		4		рF	
C <sub>io(ON)</sub>		$V_{IN} = V_{CC}$ or GND	$V_{I/O} = GND$		12		рг	
		$V_{CC} = 2.3 \text{ V}$ , TYP at $V_{CC} = 2.5 \text{ V}$ ,	I <sub>O</sub> = 24 mA		5	8	Ω	
<b>-</b> (5)		V <sub>1</sub> = 0	I <sub>O</sub> = 16 mA		5	8		
r <sub>on</sub> <sup>(5)</sup>		V 2V V 0	I <sub>O</sub> = 64 mA		5	7		
		$V_{CC} = 3 \text{ V}, V_I = 0$	I <sub>O</sub> = 32 mA		5	7		

- $\begin{array}{lll} \hbox{(1)} & V_{IN} \mbox{ and } I_{IN} \mbox{ refer to control inputs. } V_{I}, \mbox{ $V_O$}, \mbox{ $I_I$}, \mbox{ and } I_O \mbox{ refer to data pins.} \\ \hbox{(2)} & \mbox{ All typical values are at $V_{CC} = 3.3$ V (unless otherwise noted), $T_A = 25^{\circ}$C.} \\ \hbox{(3)} & \mbox{ For I/O ports, the parameter $I_{OZ}$ includes the input leakage current.} \\ \end{array}$

- (4) This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V<sub>CC</sub> or GND.
   (5) Measured by the voltage drop between A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

## **Switching Characteristics**

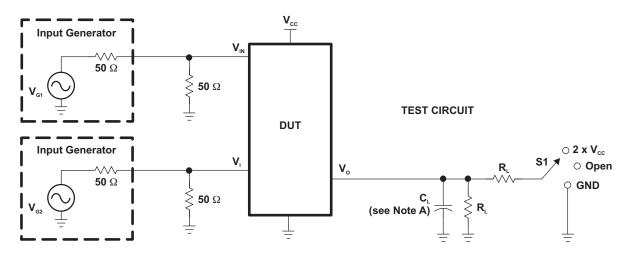
over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 2 ± 0.2	2.5 V 2 V	V <sub>CC</sub> = 3 ± 0.3	UNIT	
	(INPOT)	(001701)	MIN	MAX	MIN	MAX	
t <sub>pd</sub> <sup>(1)</sup>	A or B	B or A		0.15		0.25	ns
t <sub>en</sub>	ŌĒ	A or B	1	7.5	1	6.5	ns
t <sub>dis</sub>	ŌE	A or B	1	5.5	1	6	ns

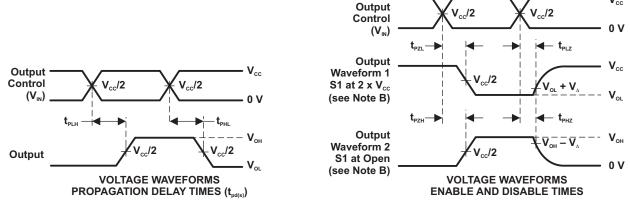
(1) The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

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#### PARAMETER MEASUREMENT INFORMATION



TEST	V <sub>cc</sub>	S1	R <sub>L</sub>	V,	C <sub>L</sub>	V <sub>Δ</sub>
t <sub>pd(s)</sub>	2.5 V ± 0.2 V 3.3 V ± 0.3 V	Open Open	500 Ω 500 Ω	3.6 V or GND 5.5 V or GND	30 pF 50 pF	
t <sub>PLZ</sub> /t <sub>PZL</sub>	$\begin{array}{c} 2.5 \; \text{V} \pm 0.2 \; \text{V} \\ 3.3 \; \text{V} \pm 0.3 \; \text{V} \end{array}$	2 x V <sub>cc</sub> 2 x V <sub>cc</sub>	500 Ω 500 Ω	GND GND	30 pF 50 pF	0.15 V 0.15 V
t <sub>PHZ</sub> /t <sub>PZH</sub>	2.5 V ± 0.2 V 3.3 V ± 0.3 V	Open Open	500 Ω 500 Ω	3.6 V 5.5 V	30 pF 50 pF	0.15 V 0.15 V



NOTES: A. C, includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_o = 50 \ \Omega$ ,  $t_r \leq 2.5 \ ns$ ,  $t_r \leq 2.5 \ ns$ .
- D. The outputs are measured one at a time, with one transition per measurement.
- E.  $t_{PLZ}$  and  $\dot{t}_{PHZ}$  are the same as  $t_{dis}$ .
- F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
- G. t<sub>PLH</sub> and t<sub>PHL</sub> are the same as t<sub>Dd(s)</sub>. The tpd propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch nd the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
- H. All parameters and waveforms are not applicable to all devices.

Figure 2. Test Circuit and Voltage Waveforms



## **TYPICAL CHARACTERISTICS**

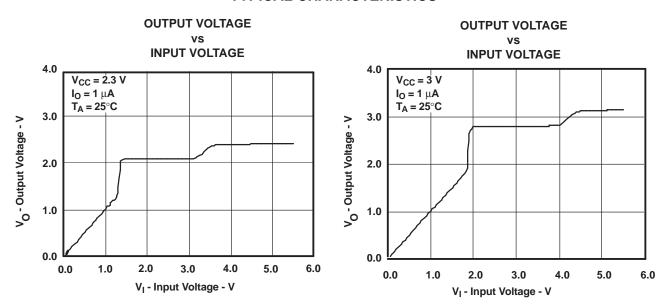
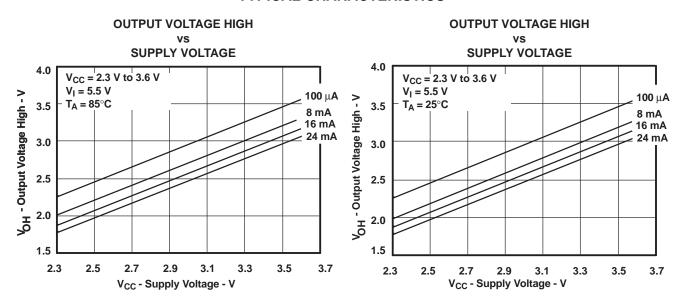


Figure 3. Data Output Voltage vs Data Input Voltage

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#### TYPICAL CHARACTERISTICS



#### **OUTPUT VOLTAGE HIGH**

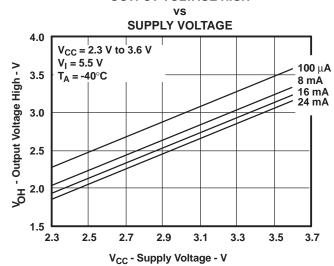


Figure 4. V<sub>OH</sub> Values





10-Dec-2020

#### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
74CB3T1G125DBVRE4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	W25F	Samples
74CB3T1G125DBVRG4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	W25F	Samples
74CB3T1G125DCKRG4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(WM5, WMF, WMJ, WM R)	Samples
SN74CB3T1G125DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 85	(W25F, W25J, W25R)	Samples
SN74CB3T1G125DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 85	(WM5, WMF, WMJ, WM R)	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



## **PACKAGE OPTION ADDENDUM**

10-Dec-2020

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF SN74CB3T1G125:

Automotive: SN74CB3T1G125-Q1

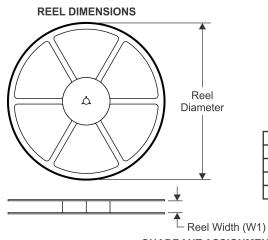
NOTE: Qualified Version Definitions:

Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

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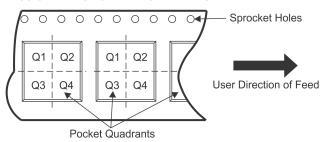
## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

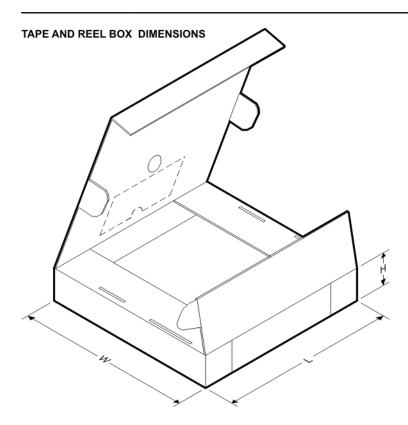
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74CB3T1G125DBVRG4	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74CB3T1G125DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74CB3T1G125DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74CB3T1G125DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74CB3T1G125DCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74CB3T1G125DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3

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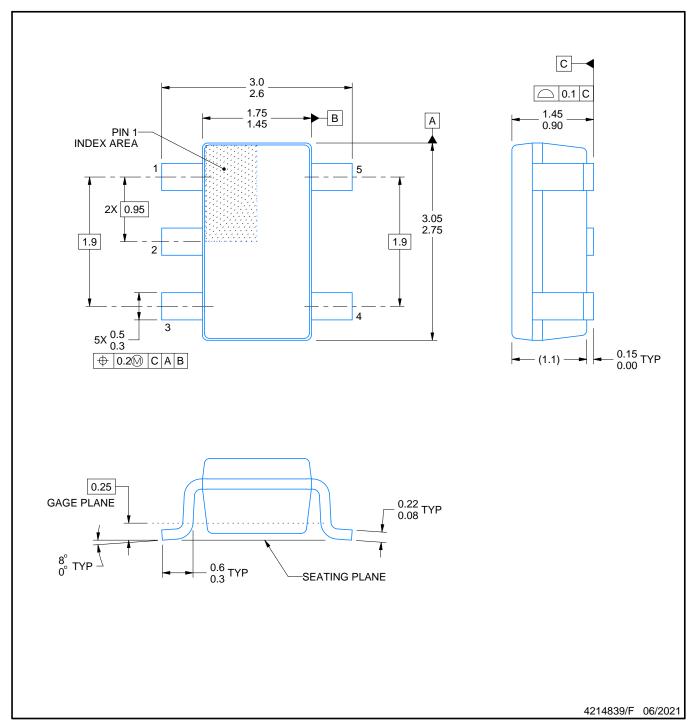


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74CB3T1G125DBVRG4	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74CB3T1G125DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0
SN74CB3T1G125DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74CB3T1G125DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74CB3T1G125DCKR	SC70	DCK	5	3000	202.0	201.0	28.0
SN74CB3T1G125DCKR	SC70	DCK	5	3000	180.0	180.0	18.0



SMALL OUTLINE TRANSISTOR



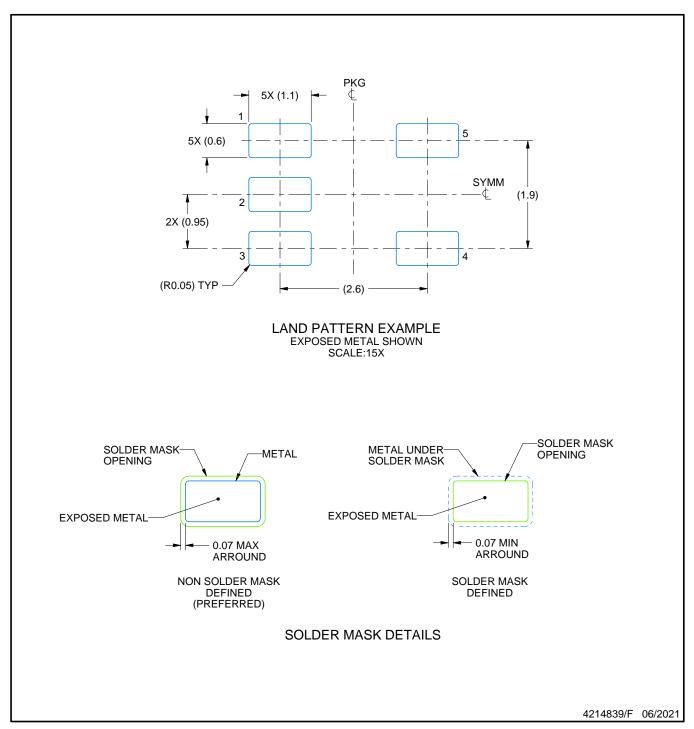
#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
  3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.



SMALL OUTLINE TRANSISTOR

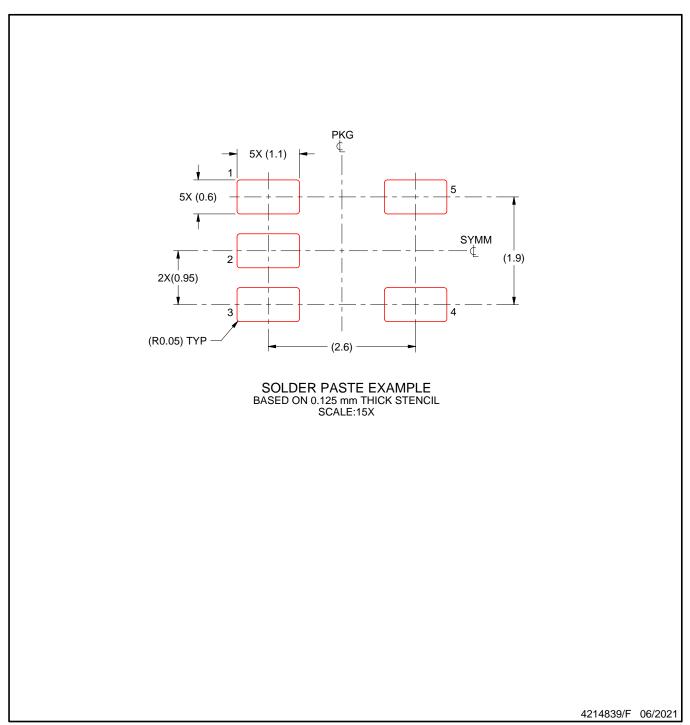


NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

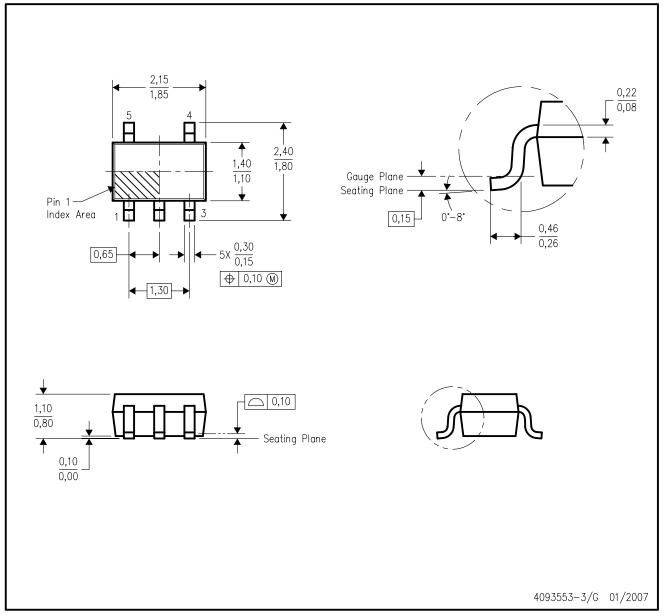


<sup>7.</sup> Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

<sup>8.</sup> Board assembly site may have different recommendations for stencil design.

# DCK (R-PDSO-G5)

## PLASTIC SMALL-OUTLINE PACKAGE



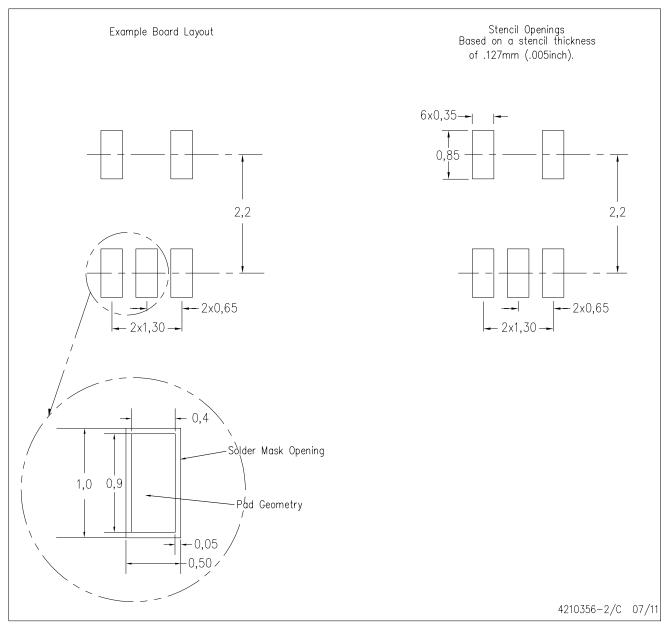
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AA.



# DCK (R-PDSO-G5)

## PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



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